

## REMARKS

Claim 7 has been amended to call for oxidizing a metallic precursor using a liquid. Specifically, the claim calls for oxidizing the metallic precursor directly on the substrate.

In the cited reference to Tsuzumitani, the item that is oxidized is the item 7 or 7a. It is not on the substrate 1. See the cited reference at column 7, line 11. Instead, it is spaced up from the substrate at least by the material 1 and the material 3.

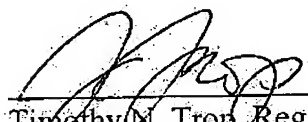
An underlayer is formed during the conventional oxidation process between the substrate and the metallic precursor. By using a liquid oxidant, in the situation where the metallic precursor is directly on the substrate, the underlayer can be reduced or avoided. See specification, page 3, lines 9-13 and page 1, lines 6-16. In other words, using conventional oxidation techniques and metallic precursor films directly on the substrate, the oxidation penetrates into the underlying substrate below the film to form undesirable dielectric underlayers with little or no controllability.

The formation of a substrate underlayer is not even an issue in the cited reference because the oxidation occurs on a layer which is well-spaced above the substrate 1. There is nothing in the cited reference which in any way suggests that the use of liquid oxidant would solve the problem addressed herein.

Therefore, the application should now be in condition for allowance.

Respectfully submitted,

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Timothy N. Trop, Reg. No. 28,994  
TROP, PRUNER & HU, P.C.  
8554 Katy Freeway, Ste. 100  
Houston, TX 77024  
713/468-8880 [Phone]  
713/468-8883 [Fax]